

⌚ Pending

 Active

L1: (188207) reference adj2 (level or voltage)
L2: (6459) read adj error
L3: (63) 1 same 2
L4: (20) 365/ and 3
L5: (43) 3 not 4
L6: (12873) reference adj2 cell
L7: (33) 2 same 6
L9: (594) 1 and 2
L10: (143) 2 and 6
L11: (1495) 365/185.03
L12: (874) 365/185.2
L13: (5966) 365/201
L14: (2106) 365/210
L15: (27) 9 and 11
L17: (28) 9 and 13
L18: (17) 9 and 14
L16: (30) 9 and 12
L19: (232) 9 and 365/
L20: (164) 19 not (15 or 16 or 17 or 18)
L21: (46) (COHEN adj2 GUY).in.

 Failed

 Saved

USPAT:US-PCFUELEPG JP0 DERWENT IEM_TOR

Default operator: OR

P Plots

P Highlight all hit items only

http://www.uspto.gov/patft/serchform/serchform.html

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	U	I	Document ID	Issue Date	Inventor	Current OR	Current XRef	Retrieval Cla	Title
1				US 6639237 B2	20031028	Takano, Yoshinori et al.	365/185.22	365/185.2; 365/185.21	Non-volatile semiconductor device
2				US 6044019 A	20000328	Cernea, Raul-Adrian et al.	365/185.21	365/185.2; 365/189.07	Non-volatile memory with sensing and method thereof
3				US 5626601 A	19981027	Hollmer, Shane C. et al.	365/185.2	365/185.22; 365/185.24	Programmed reference
4				US 5605500 A	19980908	Campardo, Giovanni et al.	365/185.2	365/185.21	Circuit and method for generating read reference signal for non-volatile memory devices
5				US 5657332 A	19970812	Audair, Daniel L. et al.	714/763	365/184; 365/189.07	Soft errors handling in EEPROM devices